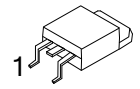
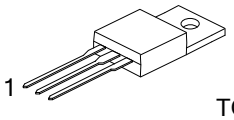
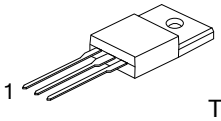
4 Amps, 900 Volts
N-CHANNEL POWER MOSFET



TO-252



TO-220



TO-220F

■ DESCRIPTION

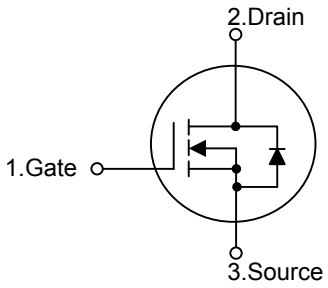
The UTC **4N90** is a N-channel enhancement MOSFET adopting UTC's advanced technology to provide customers with DMOS, planar stripe technology. This technology is designed to meet the requirements of the minimum on-state resistance and perfect switching performance. It also can withstand high energy pulse in the avalanche and communication mode.

The UTC **4N90** is particularly applied in high efficiency switch mode power supplies.

■ FEATURES

* V_{DS}=900V
* I_D=4A
* $R_{DS(ON)}$=4.2Ω @ V_{GS}=10V
* Typically 17nC low gate charge
* High switching speed
* Typically 5.6pF low C_{RSS}
* 100% avalanche tested
* Improved dv/dt capability

■ SYMBOL



■ ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
4N90L-TA3-T	4N90G-TA3-T	TO-220	G	D	S	Tube
4N90L-TF3-T	4N90G-TF3-T	TO-220F	G	D	S	Tube
4N90L-TN3-R	4N90G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

4N90L - TA3 - T (1) Packing Type (2) Package Type (3) Lead Free	(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF3: TO-220F, TN3: TO-252 (3) G: Halogen Free, L: Lead Free

■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER			SYMBOL	RATINGS	UNIT
Drain to Source Voltage			V_{DSS}	900	V
Gate to Source Voltage			V_{GSS}	±30	V
Avalanche Current (Note 2)			I_{AR}	4	A
Continuous Drain Current	Continuous		I_D	4	A
	Pulsed (Note 2)		I_{DM}	16	A
Avalanche Energy	Single Pulsed (Note 3)		E_{AS}	570	mJ
	Repetitive (Note 2)		E_{AR}	14	mJ
Peak Diode Recovery dv/dt (Note 4)			dv/dt	4.5	V/ns
Power Dissipation(T_C=25°C)		TO-220	P_D	140	W
		TO-220F		47	
		TO-252		54	
Derate above 25°C		TO-220		1.12	W/°C
		TO-220F		0.38	
		TO-252		0.43	
Operating Junction Temperature			T_J	+150	°C
Storage Temperature			T_{STG}	-55 ~ +150	°C

Note : 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature
3. L=67mH, I_{AS}=4A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C
4. I_{SD} ≤4A, di/dt ≤200A/μs, V_{DD} ≤BV_{DSS}, Starting T_J=25°C

■ THERMAL DATA

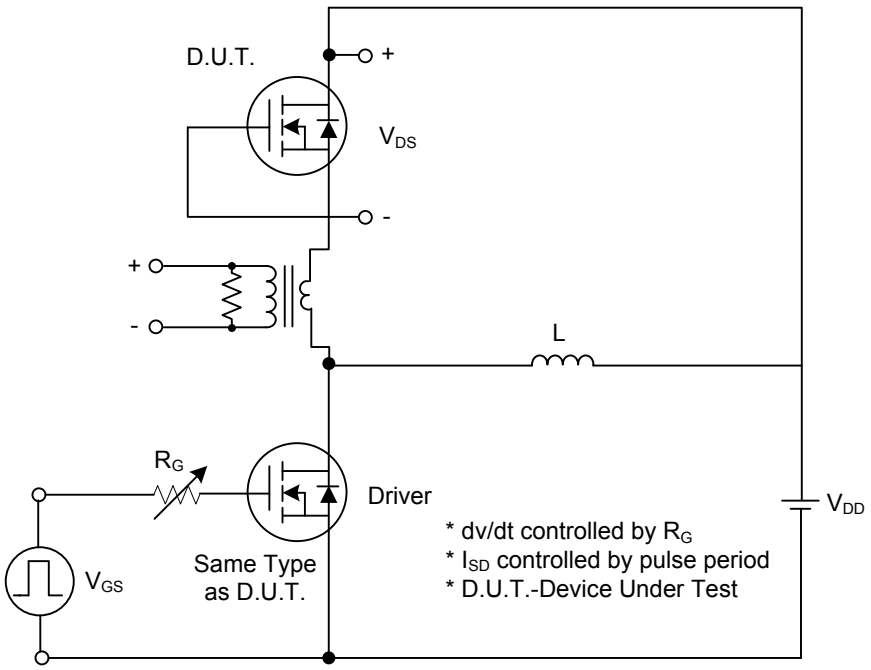
PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220	θ_{JA}	62.5	°C/W
	TO-220F		62.5	
	TO-252		110	
Junction to Case	TO-220	θ_{JC}	0.89	°C/W
	TO-220F		2.66	
	TO-252		2.3	

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

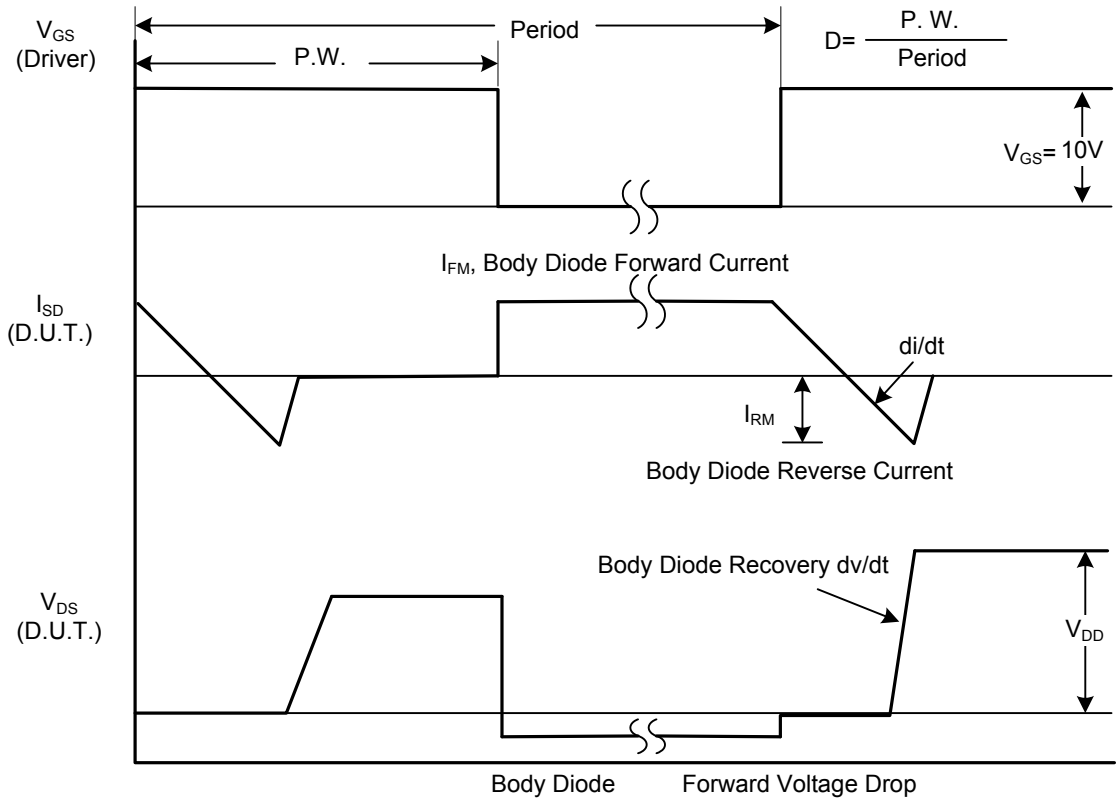
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0V, I_D=250μA	900			V
Breakdown Voltage Temperature Coefficient		$\Delta BV_{DSS}/\Delta T_J$	I_D=250μA, Referenced to 25°C		1.05		V/°C
Drain-Source Leakage Current		I_{DSS}	V_{DS}=900V, V_{GS}=0V			10	μA
			V_{DS}=720V, T_C=125°C			100	μA
Gate- Source Leakage Current	Forward	I_{GSS}	V_{GS}=+30V, V_{DS}=0V			+100	nA
	Reverse	I_{GSS}	V_{GS}=-30V, V_{DS}=0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=250μA	3.0		5.0	V
Drain-Source On-State Resistance		$R_{DS(ON)}$	V_{GS}=10V, I_D=2A		3.5	4.2	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{DS}=25V,V_{GS}=0V,f=1.0MHz		740	960	pF
Output Capacitance		C_{OSS}			65	85	pF
Reverse Transfer Capacitance		C_{RSS}			5.6	7.3	pF
SWITCHING PARAMETERS							
Total Gate Charge		Q_G	V_{DS}=720V, V_{GS}=10V, I_D=4A (Note 1,2)		17	22	nC
Gate-Source Charge		Q_{GS}			4.5		nC
Gate-Drain Charge		Q_{GD}			7.5		nC
Turn-ON Delay Time		$t_{D(ON)}$	V_{DD}=450V, I_D=4A, R_G=25Ω (Note 1,2)		25	60	ns
Turn-ON Rise Time		t_R			50	110	ns
Turn-OFF Delay Time		$t_{D(OFF)}$			40	90	ns
Turn-OFF Fall Time		t_F			35	80	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				4	A
Maximum Body-Diode Pulsed Current		I_{SM}				16	A
Drain-Source Diode Forward Voltage		V_{SD}	I_S =4A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time		t_{RR}	V_{GS}=0V, I_S=4A, dI_F/dt=100A/μs (Note 1)		450		ns
Body Diode Reverse Recovery Charge		Q_{RR}			3.5		μC

Note : 1. Pulse Test : Pulse width≤300μs, Duty cycle≤2%
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

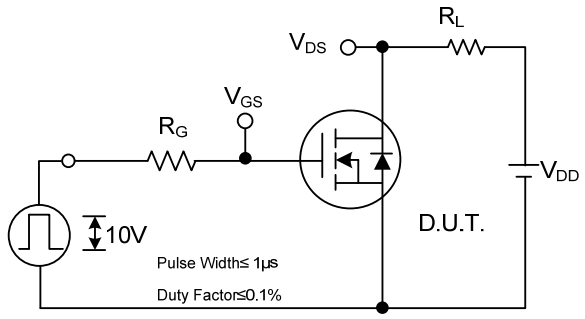


Peak Diode Recovery dv/dt Test Circuit

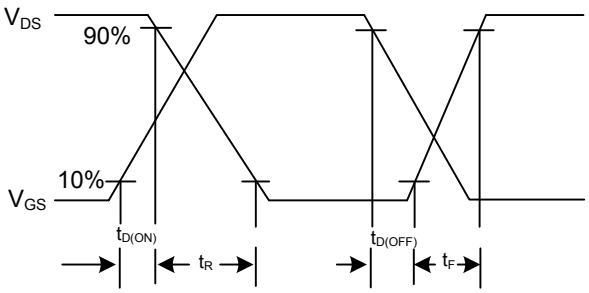


Peak Diode Recovery dv/dt Waveforms

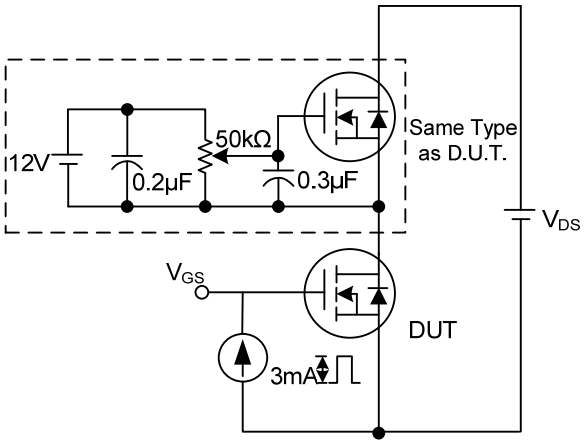
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



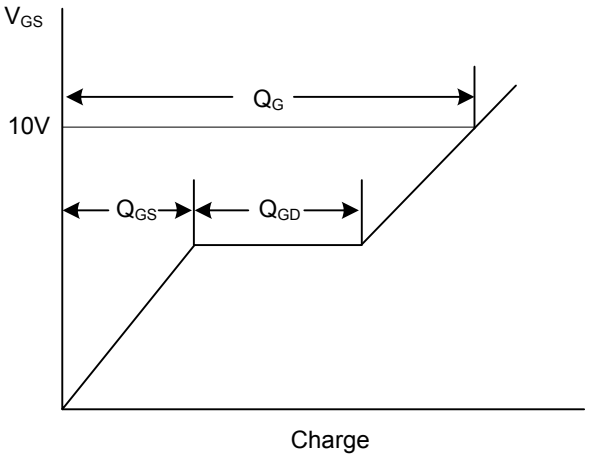
Switching Test Circuit



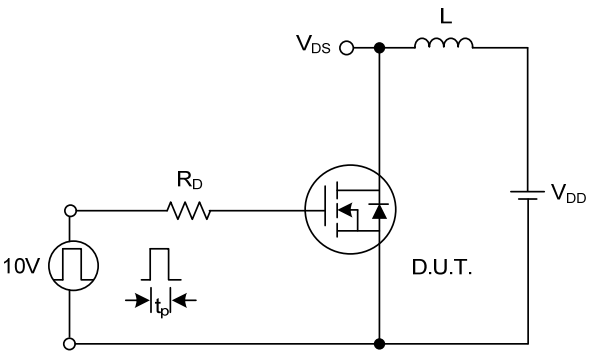
Switching Waveforms



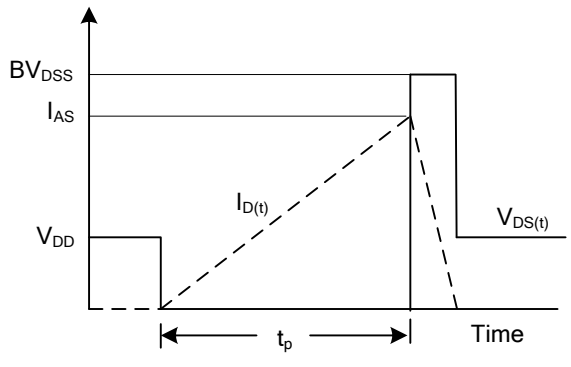
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms